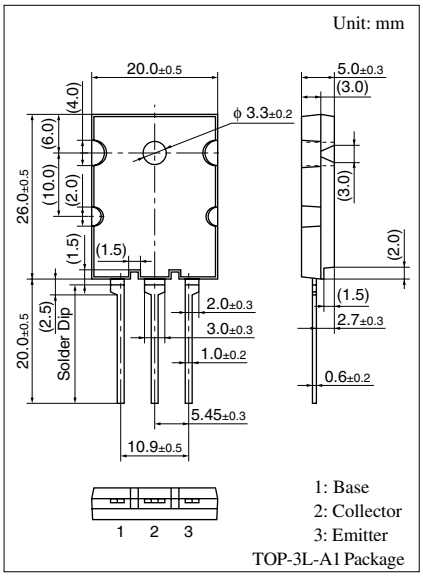
2SD2276

Silicon NPN triple diffusion planar type Darlington

For power amplification
Complementary to 2SB1503



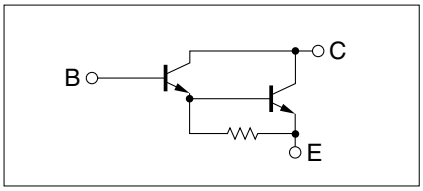
■ Features

- Optimum for 110 W Hi-Fi output
- High forward current transfer ratio h_{FE}: 5 000 to 30 000
- Low collector to emitter saturation voltage $V_{CE(sat)}$: < 2.5 V

■ Absolute Maximum Ratings $T_C = 25°C$

Parameter		Symbol	Rating	Unit
Collector to base voltage		V_{CBO}	160	V
Collector to emitter voltage		V_{CEO}	140	V
Emitter to base voltage		V_{EBO}	5	V
Peak collector current		I_{CP}	15	A
Collector current		I_C	8	A
Collector power dissipation	$T_C = 25°C$	P_C	120	W
	$T_a = 25°C$		3.5	
Junction temperature		T_j	150	°C
Storage temperature		T_{stg}	−55 to +150	°C

Internal Connection



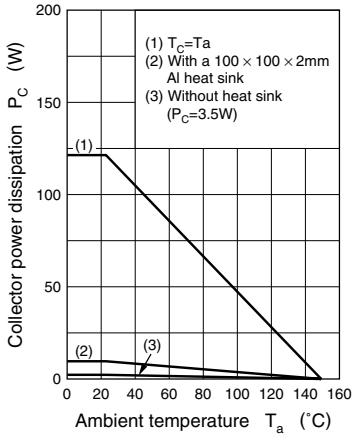
■ Electrical Characteristics $T_C = 25°C$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = 160 V, I_E = 0			100	µA
	I_{CEO}	V_{CE} = 140 V, I_B = 0			100	µA
Emitter cutoff current	I_{EBO}	V_{EB} = 5 V, I_C = 0			100	µA
Collector to emitter voltage	V_{CEO}	I_C = 30 mA, I_B = 0	140			V
Forward current transfer ratio	h_{FE1}	V_{CE} = 5 V, I_C = 1 A	2 000			
	h_{FE2} *	V_{CE} = 5 V, I_C = 7 A	5 000		30 000	
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = 7 A, I_B = 7 mA			2.5	V
Base to emitter saturation voltage	$V_{BE(sat)}$	I_C = 7 A, I_B = 7 mA			3.0	V
Transition frequency	f_T	V_{CE} = 10 V, I_C = 0.5 A, f = 1 MHz		20		MHz
Turn-on time	t_{on}	I_C = 7 A, I_{B1} = 7 mA, I_{B2} = −7 mA,		2.0		µs
Storage time	t_{stg}	V_{CC} = 50 V		6.0		µs
Fall time	t_f			1.2		µs

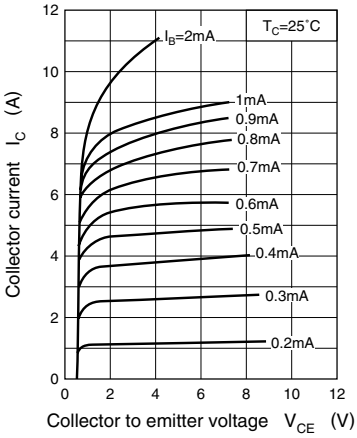
Note) ∗: Rank classification

Rank	Q	S	P
h_{FE2}	5 000 to 15 000	7 000 to 21 000	8 000 to 30 000

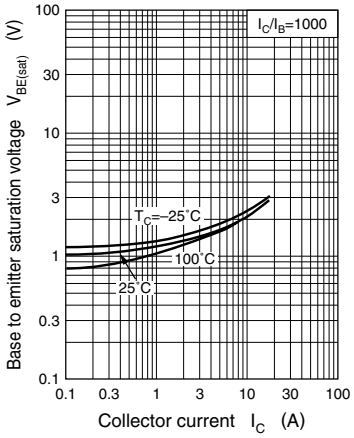
P_C — T_a



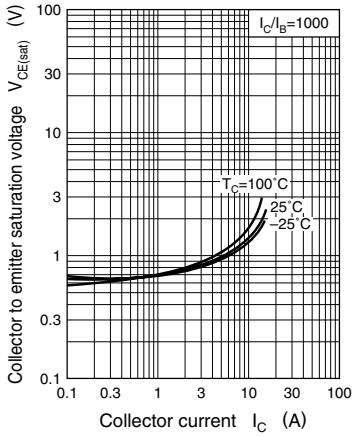
I_C — V_{CE}



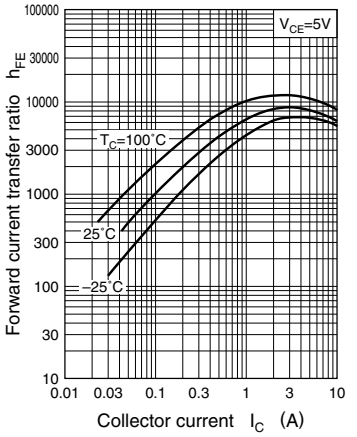
$V_{BE(sat)}$ — I_C



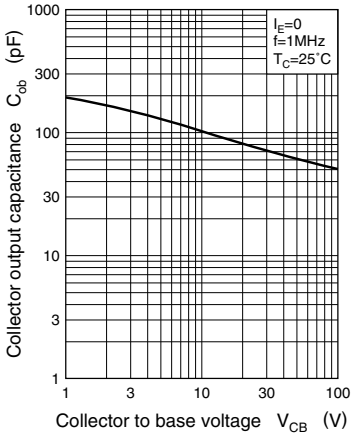
$V_{CE(sat)}$ — I_C



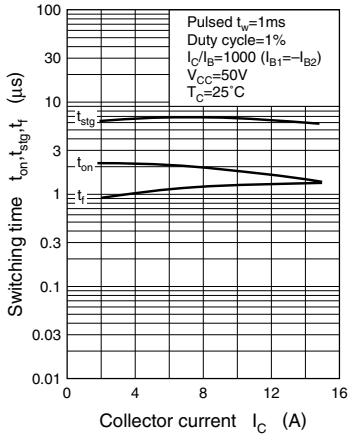
h_{FE} — I_C



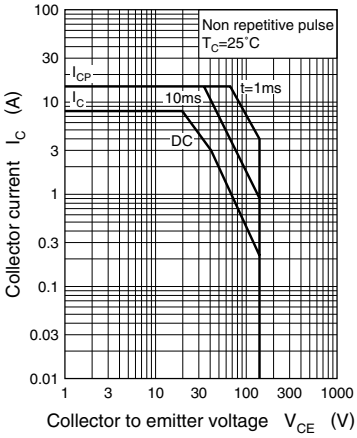
C_{ob} — V_{CB}



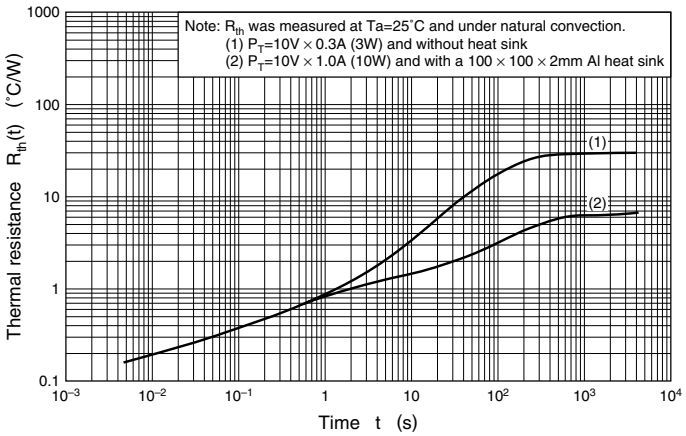
t_{on}, t_{stg}, t_f — I_C



Area of safe operation (ASO)



$R_{th(t)}$ — t


Note: R_{th} was measured at Ta=25°C and under natural convection.
(1) P_T=10V × 0.3A (3W) and without heat sink
(2) P_T=10V × 1.0A (10W) and with a 100 × 100 × 2mm Al heat sink
Thermal resistance R_{th}(t) (°C/W)
1000
100
10
1
0.1
10^{-3}
10^{-2}
10^{-1}
1
10
10^2
10^3
10^4
Time t (s)
(1)
(2)

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